

AMENDMENTS TO THE SPECIFICATION

Please replace the last paragraph on page 17 bridging page 18 of the specification with the following new paragraph:

The gallium nitride compound semiconductor stacked structure employed for fabricating the light-emitting device was produced through the following procedure: an AlN buffer layer 2 was formed on a sapphire substrate 1; and an n-type GaN contact layer 3a, an n-type GaN lower cladding layer 3b, an InGaN light-emitting layer 4, a p-type AlGaN upper cladding layer 5b, and a p-type GaN contact layer 5a, positive-electrode-metal-containing layer 6, a contact metal layer 11 which includes a semiconductor-metal-containing layer 7 were successively formed atop the buffer layer 2. The contact layer 3a is composed of n-type GaN doped with Si ($7 \times 10^{18}/\text{cm}^3$), the lower cladding layer 3b is composed of n-type GaN doped with Si ($5 \times 10^{18}/\text{cm}^3$), and the light-emitting layer 4, having a single quantum well structure, is composed of $\text{In}_{0.95}\text{Ga}_{0.05}\text{N}$. The upper cladding layer 5b is composed of p-type $\text{Al}_{0.25}\text{Ga}_{0.75}\text{N}$ doped with Mg ($1 \times 10^{18}/\text{cm}^3$). The contact layer 5a is composed of p-type GaN doped with Mg ($5 \times 10^{19}/\text{cm}^3$). Stacking of these layers was performed by means of MOCVD under typical conditions which are well known in the art.